

Features

- Advanced Shield Gate Trench technology
- Super Low Gate Charge
- High-Speed Switching
- 100% EAS Guaranteed
- Green Device Available

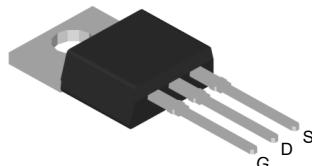
Product Summary



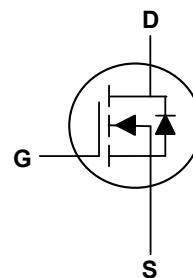
V_{DS}	150	V
I_D	125	A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	14	mΩ

Applications

- High Frequency Point-of-Load,Synchronous Buck Converter
- Networking DC-DC Power System
- Load Switch



TO-220 Top View



Absolute Maximum Ratings($T_c=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ¹	$I_D @ T_c = 25^\circ\text{C}$	125	A
Continuous Drain Current ¹	$I_D @ T_c = 100^\circ\text{C}$	80	A
Pulsed Drain Current ²	I_{DM}	500	A
Single Pulse Avalanche Energy ³	E_{AS}	1320	mJ
Total Power Dissipation	P_D	420	W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	---	0.29	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}$, $I_D=250\mu\text{A}$	150	---	---	V
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}$, $I_D=30\text{A}$	---	11	14	$\text{m}\Omega$
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}$, $I_D = 250\mu\text{A}$	2.5	---	4.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{\text{DS}}=150\text{V}$, $V_{\text{GS}}=0\text{V}$	---	---	1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 20\text{V}$, $V_{\text{DS}}=0\text{V}$	---	---	± 100	nA
Forward Transconductance	g_{fs}	$V_{\text{DS}}=5\text{V}$, $I_D=30\text{A}$	---	52	---	S
Total Gate Charge	Q_g	$V_{\text{DS}}=75\text{V}$, $V_{\text{GS}}=10\text{V}$, $I_D=30\text{A}$	---	68	---	nC
Gate-Source Charge	Q_{gs}		---	23	---	
Gate-Drain Charge	Q_{gd}		---	24	---	
Turn-On Delay Time	$T_{\text{d}(\text{on})}$	$V_{\text{DD}}=75\text{V}$, $V_{\text{GS}}=10\text{V}$, $R_G=3\Omega$, $I_D=30\text{A}$	---	18	---	ns
Rise Time	T_r		---	89	---	
Turn-Off Delay Time	$T_{\text{d}(\text{off})}$		---	34	---	
Fall Time	T_f		---	70	---	
Input Capacitance	C_{iss}	$V_{\text{DS}}=75\text{V}$, $V_{\text{GS}}=0\text{V}$, $f=1\text{MHz}$	---	3500	---	pF
Output Capacitance	C_{oss}		---	310	---	
Reverse Transfer Capacitance	C_{rss}		---	85	---	

Drain-Source Diode Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Diode Forward Voltage ²	V_{SD}	$V_{\text{GS}}=0\text{V}$, $I_s=30\text{A}$, $T_J=25^\circ\text{C}$	---	---	1.3	V
Reverse Recovery Time	t_{rr}	$I_F=30\text{A}$	---	70	---	nS
Reverse Recovery Charge	Q_{rr}		---	230	---	nC

Note:

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{\text{DD}}=50\text{V}$, $L=0.5\text{mH}$

Typical Characteristics

Fig 1: Output Characteristics

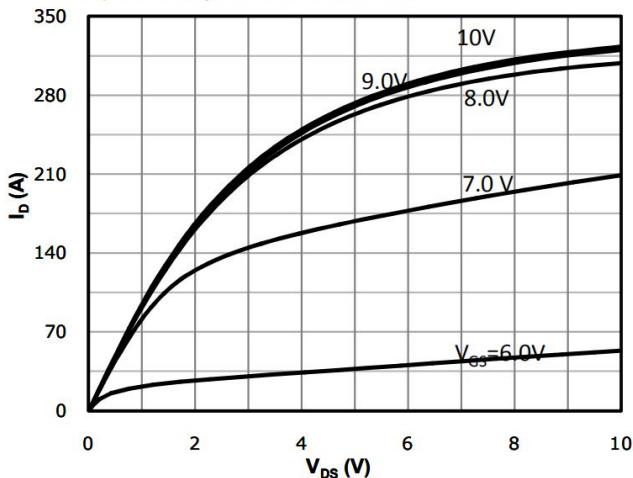


Fig 2: Transfer Characteristics

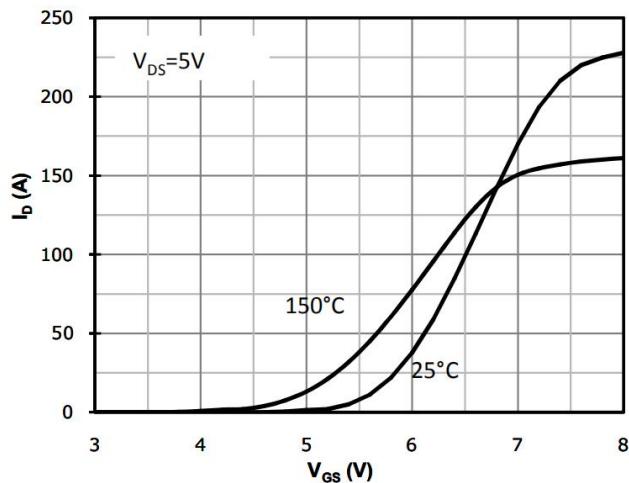


Fig 3: R_{ds(on)} vs Drain Current and Gate Voltage

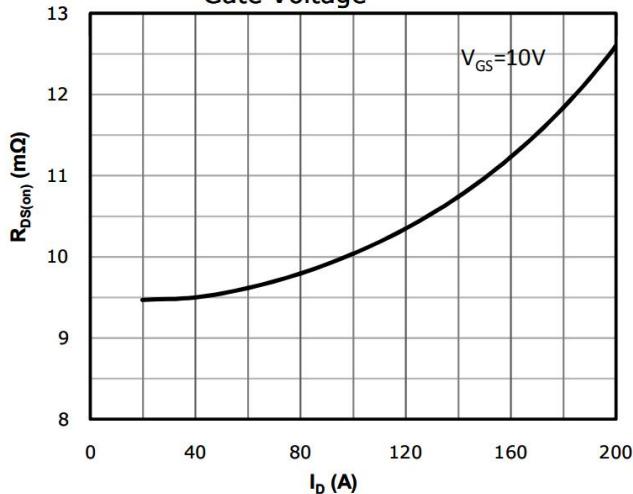


Fig 4: R_{ds(on)} vs Gate Voltage

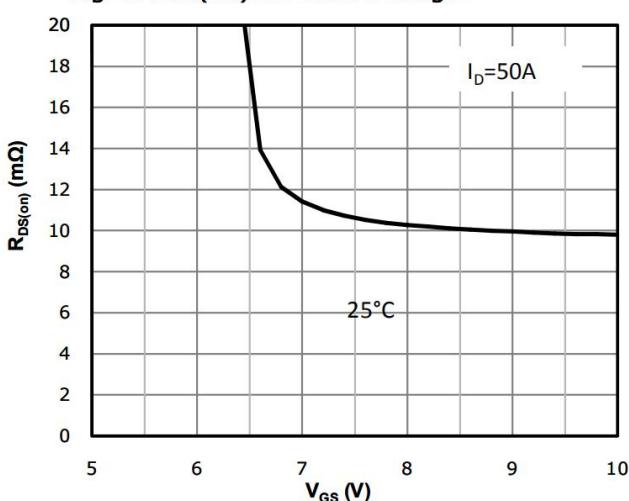


Fig 5: R_{ds(on)} vs. Temperature

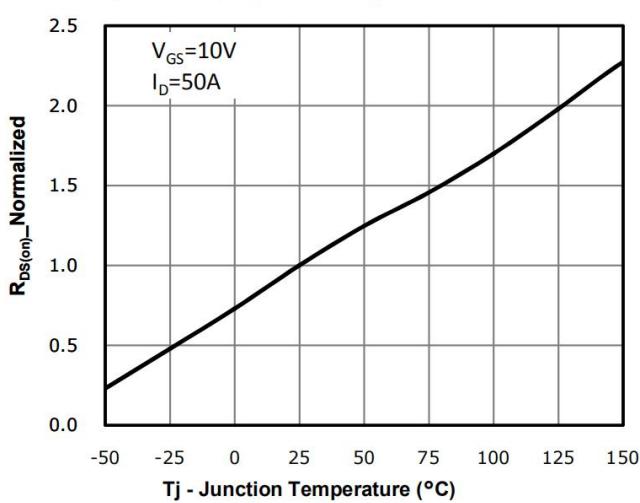


Fig 6: Capacitance Characteristics

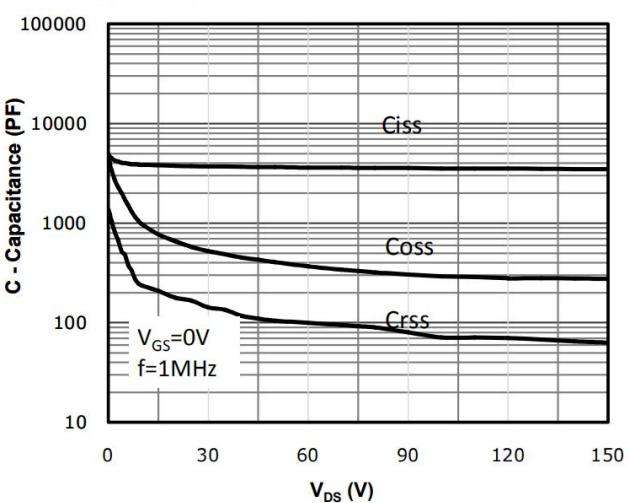
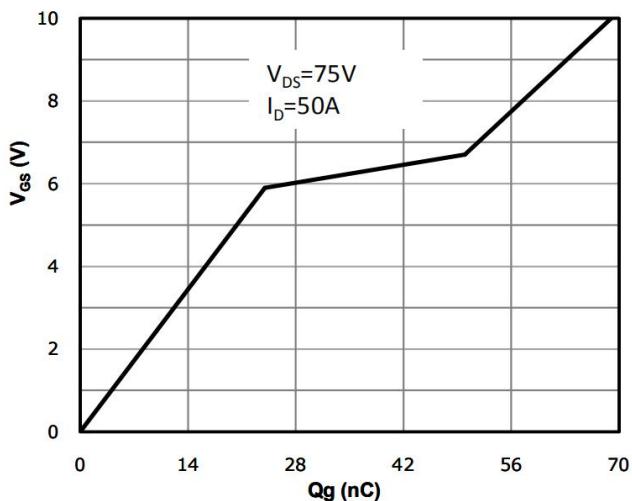
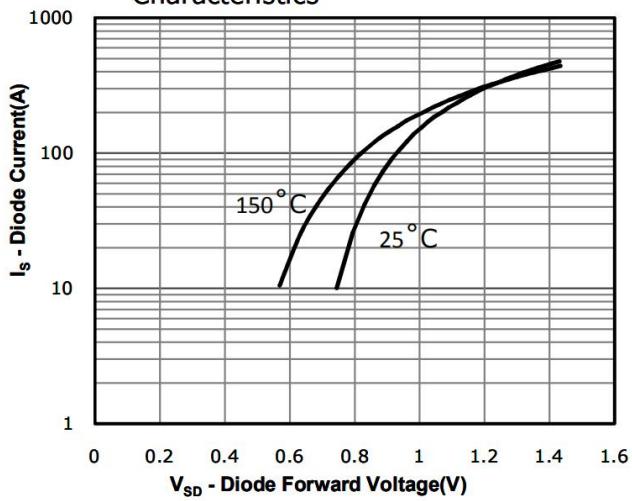
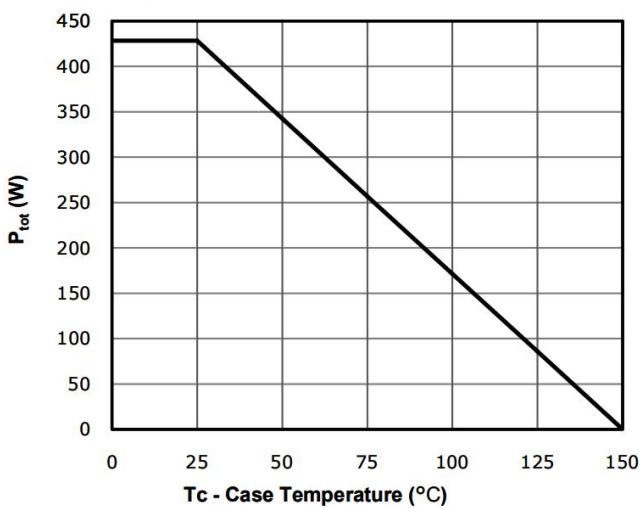
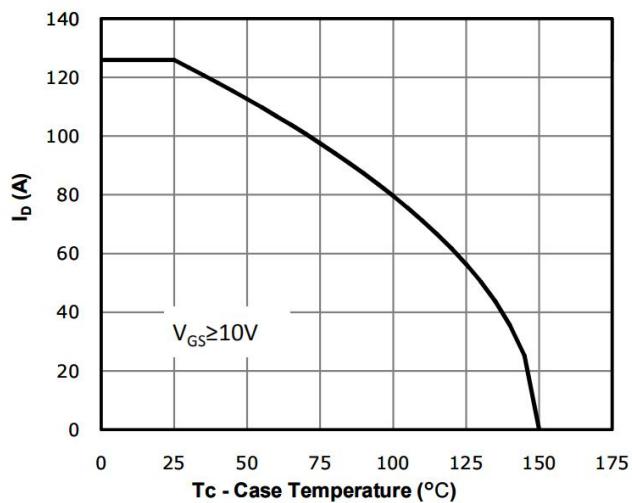
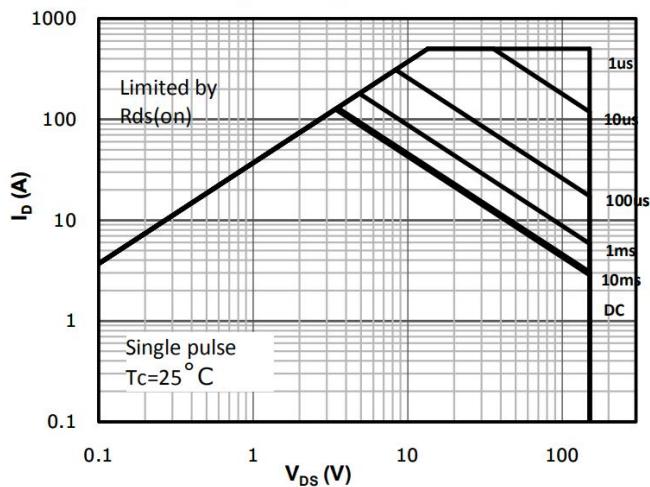
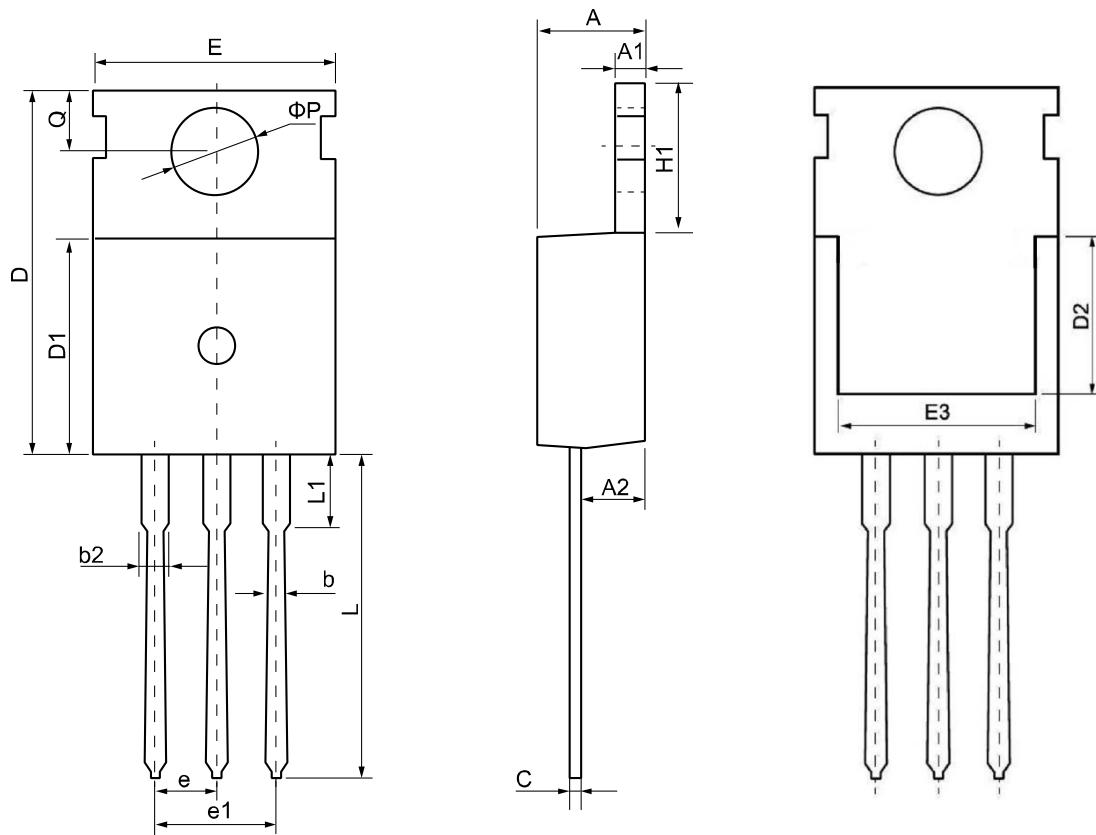


Fig 7: Gate Charge Characteristics

Fig 8: Body-diode Forward Characteristics

Fig 9: Power Dissipation

Fig 10: Drain Current Derating

Fig 11: Safe Operating Area


TO-220 Package Outline Dimensions



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	4.30	4.55	4.75	E	9.65	10.00	10.25
A1	1.15	1.30	1.45	E3	7.00	--	--
A2	2.20	2.40	2.60	e	2.54 BSC		
b	0.70	0.80	0.95	e1	5.08 BSC		
b2	1.17	1.27	1.47	H1	6.30	6.50	6.80
c	0.40	0.50	0.65	L	12.70	13.50	14.10
D	15.30	15.60	15.90	L1	--	3.20	3.95
D1	8.90	9.10	9.35	φP	3.40	3.60	3.80
D2	5.50	--	--	Q	2.60	2.80	3.00